#### SILICON (Si) POWER MOSFET A CEM1008SL



# **CEM1008SL**

# 100V ▲ 100mΩ ▲ 2.9A ▲ Dual Si MOSFET

SILICON Si MOSFET ▲ SMD type Dual N-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





HALOGEN

FREE

RoHS

#### **MAXIMUM RATINGS**

Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	100V
Gate-Source Voltage	V <sub>GS</sub>	±16V
Continuous Drain Current	Ι <sub>D</sub>	2.9A
Pulsed Drain Current Note 1	I <sub>DM</sub>	11.6A
Maximum Power Dissipation	PD	2W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	62.5°C/W

#### **APPLICATIONS**

Audio	DC	Industrial	Power over	Synchronous
Amplifier	Fan	Control	Ethernet	Rectification
<b>(</b> )			PoE	

#### **PIN DESCRIPTION**

Circuit Diagram	Outline • Top View	Pin No.	Description
$\begin{array}{c} D_{1}(7,8) \\ \hline \\ G_{1}(2) \\ \hline \\ S_{1}(1) \end{array} \qquad \begin{array}{c} D_{2}(5,6) \\ \hline \\ G_{2}(4) \\ \hline \\ S_{2}(3) \end{array}$		1 2 3 4 5 6 7 8	Source MOSFET 1 Gate MOSFET 1 Source MOSFET 2 Gate MOSFET 2 Drain MOSFET 2 Drain MOSFET 2 Drain MOSFET 1 Drain MOSFET 1

CEM1008SL Rev.001 Date: 30/09/2022 Page: 1

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# **ELECTRICAL CHARACTERISTICS A T**<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV <sub>DSS</sub>	100			V
Zero Gate Voltage Drain Current	$V_{DS}$ = 100V, $V_{GS}$ = 0V	I <sub>DSS</sub>			1	μA
Gate Body Leakage Current, Forward	$V_{GS}$ = 16V, $V_{DS}$ = 0V	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -16V, V_{DS} = 0V$	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	$V_{GS(th)}$	0.4		1.4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V$ , $I_D = 2A$	R <sub>DS(ON)</sub>		100	120	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 5V$ , $I_D = 2A$	R <sub>DS(ON)</sub>		105	130	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 3V$ , $I_D = 1A$	R <sub>DS(ON)</sub>		112	145	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		475		pF
Output Capacitance	$V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1MHz	Coss		120		pF
Reverse Transfer Capacitance	$V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		40		рF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{\text{G}(\text{ext})}$ = 6 $\Omega$	t <sub>D(ON)</sub>		9		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(\text{ext})}$ = 6 $\Omega$	t <sub>R</sub>		4		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(\text{ext})}$ = 6 $\Omega$	t <sub>D(OFF)</sub>		46		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 50V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(ext)}$ = 6 $\Omega$	t <sub>F</sub>		17		ns
Total Gate Charge	$V_{\text{DS}}$ = 80V, $V_{\text{GS}}$ = 4.5V, $I_{\text{D}}$ = 2A	Q <sub>G</sub>		9.8		nC
Gate Source Charge	$V_{DS}$ = 80V, $V_{GS}$ = 4.5V, $I_{D}$ = 2A	Q <sub>GS</sub>		0.6		nC
Gate Drain Charge	$V_{DS}$ = 80V, $V_{GS}$ = 4.5V, $I_{D}$ = 2A	$\mathbf{Q}_{GD}$		4.5		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		Is			1.6	А
Drain-Source Diode Forward Voltage <sup>Note 3</sup>	$V_{GS} = 0V$ , $I_S = 1A$	$V_{\text{SD}}$			1.2	V

#### Notes

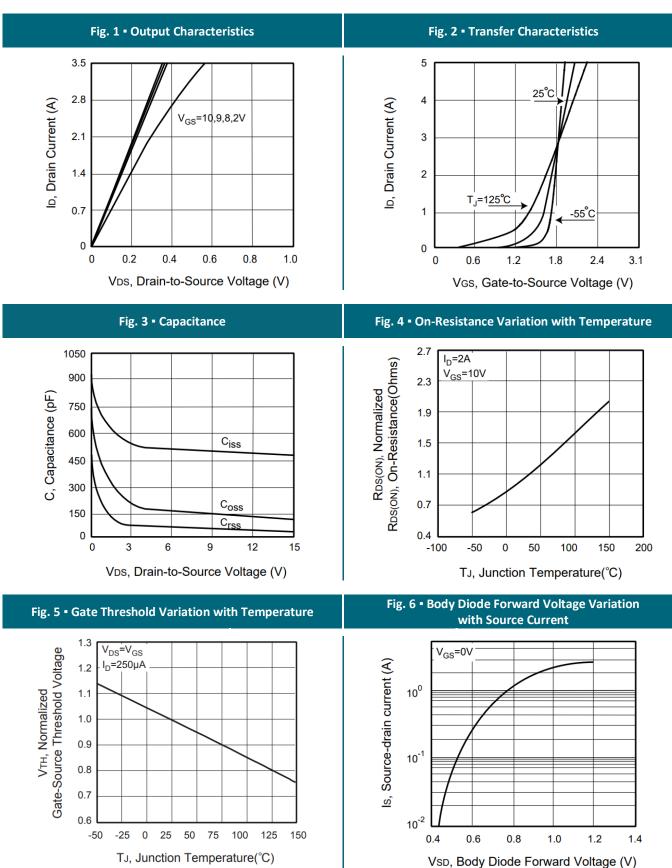
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board,  $t \le 10$  sec
- 3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4: Guaranteed by design, not subject to production testing.



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## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



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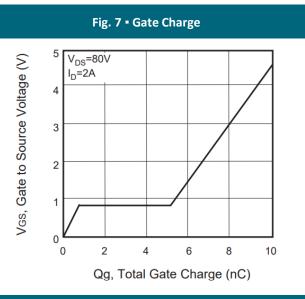


Fig. 9 - Breakdown Voltage Variation vs. Temperature

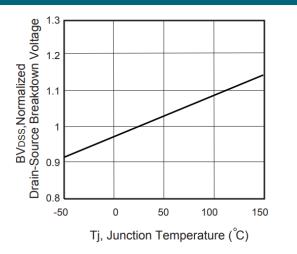


Fig. 10 - Switching Test Circuit

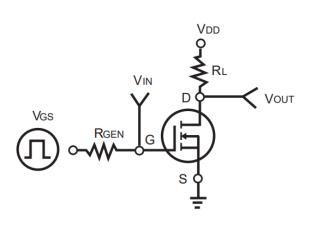
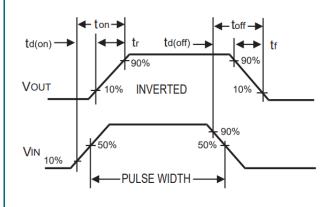


Fig. 8 • Maximum Safe Operating Area 10<sup>2</sup> R<sub>DS(ON)</sub>Limit ID, Drain Current (A) 10<sup>1</sup> 10ms 100ms 10<sup>0</sup> 10 T<sub>A</sub>=25℃ T\_=150°C Single Pulse 10<sup>-2</sup> 10<sup>-1</sup> 10<sup>0</sup> 10<sup>1</sup>  $10^{2}$  $10^{3}$ VDS, Drain-Source Voltage (V)

Fig. 11 • Switching Waveforms



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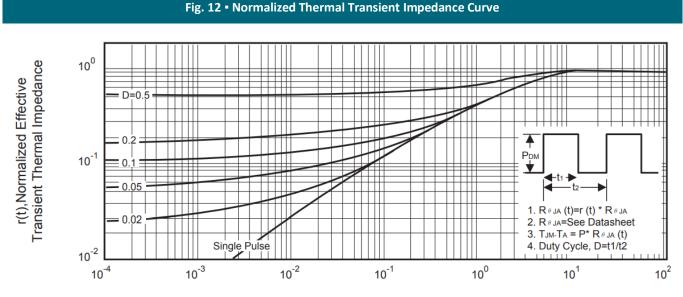
CEM1008SL ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 4

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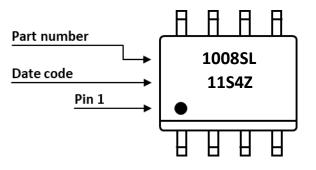
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# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



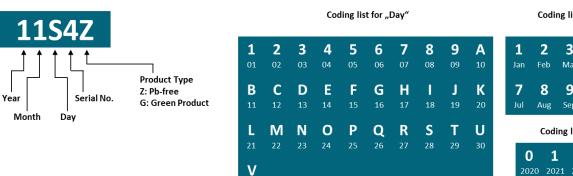
Square Wave Pulse Duration (sec)

#### **PART MARKING**



#### DATE CODE

Example: 11S4Z

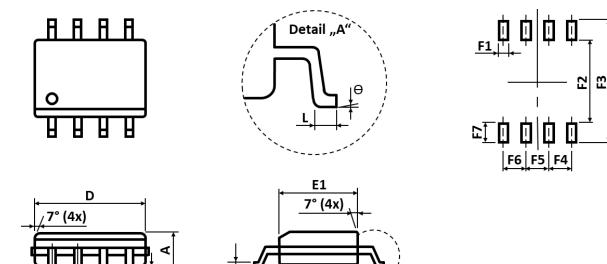






• Detail "A"

## PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Sym	Millimeters	Millimeters		Sym	Millimeters	Millimeters	Millimeters

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	I
Г1		0 5 0 0				1 270		
F1	-	0.500	-	F5	-	1.270	-	
F2	-	4.250	-	F6	-	1.270	-	
F3	-	6.250	-	F7	-	1.000	-	
F4	-	1.270	-					

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

# **ORDERING INFORMATION**

В

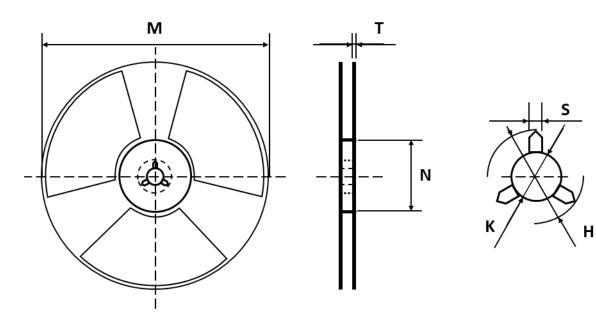
A1

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM1008SL	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs



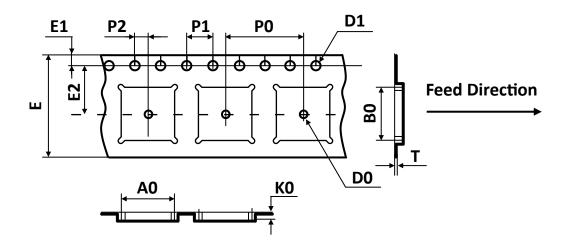


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	Ν	т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	<b>\$550</b>	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

#### **TAPE DIMENSIONS** All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

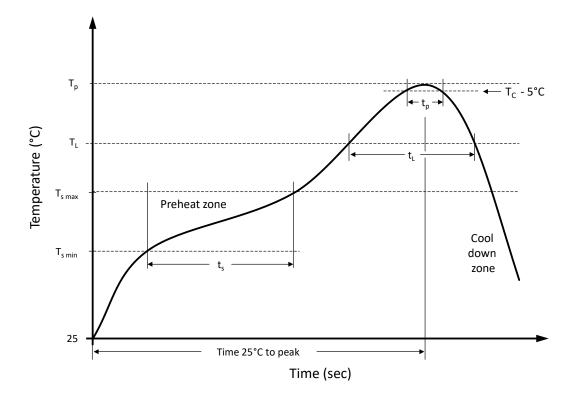
Note: All dimensions meet EIA-481-D requirements.

CEM1008SL ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 7





#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

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# **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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